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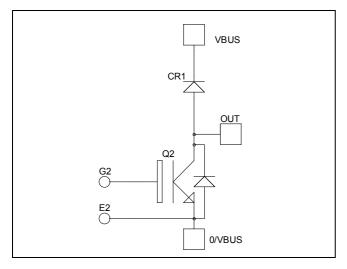
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

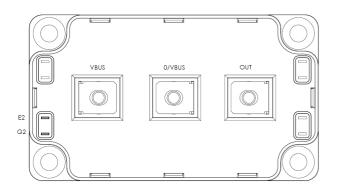




APTGT600DA60G

Boost chopper Trench + Field Stop IGBT3 Power Module





$V_{CES} = 600V$ $I_{C} = 600A^{*}$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features •

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
 - High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance

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- Easy paralleling due to positive TC of VCEsat
- Low profile

Mars and a

RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	700 *	
	Continuous Conector Current	$T_C = 80^{\circ}C$	600 *	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	800	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2300	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	1200A @ 550V	

* Specification of IGBT device but output current must be limited to 500A to not exceed a delta of temperature greater than 100°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				750	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 600A$	$T_j = 25^{\circ}C$		1.4	1.8	V
			$T_{j} = 150^{\circ}C$		1.5		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				800	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			49			
Coes	Output Capacitance				3.1		nF	
C _{res}	Reverse Transfer Capacitance				1.5			
T _{d(on)}	Turn-on Delay Time	Inductive Switch	ning (25°C)		130			
Tr	Rise Time	$V_{GE} = \pm 15V$			55			
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 600A$			250		ns	
$T_{\rm f}$	Fall Time	$R_G = 2\Omega$		60				
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 600A$ $R_G = 2\Omega$			145		ns	
T _r	Rise Time				60			
T _{d(off)}	Turn-off Delay Time				320			
$T_{\rm f}$	Fall Time				80			
Б	Turn on Enormy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		3		T	
Eon	Turn on Energy	$V_{Bus} = 300V$	$T_{j} = 150^{\circ}C$		5.5		mJ	
Б	Turn off Energy	$I_{\rm C} = 600 {\rm A}$	$T_j = 25^{\circ}C$		17		mJ	
E _{off}	Turn on Energy	$R_G = 2\Omega$	$R_G = 2\Omega \qquad \qquad T_j = 150^\circ$	$R_G = 2\Omega$ $T_j = 150^{\circ}C$		21		IIIJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			350 550	μΑ
I _F	DC Forward Current		$T_c = 80^{\circ}C$		600	220	А
$V_{\rm F}$	Diada Forward Voltage	de Forward Voltage $I_F = 600 \text{A}$ $V_{GE} = 0 \text{V}$	$T_i = 25^{\circ}C$		1.5	1.9	V
V F	Didde Forward Voltage		$T_{i} = 150^{\circ}C$		1.4		
t _{rr}	Reverse Recovery Time	$I_{F} = 600A$ $V_{R} = 300V$ $di/dt = 5000A/\mu s$	$T_j = 25^{\circ}C$		120		ns
ι _{rr}			$T_{j} = 150^{\circ}C$		210		
0	Reverse Recovery Charge		$T_j = 25^{\circ}C$		27		чС
Q _{rr}			$T_{i} = 150^{\circ}C$		57		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		6.9		mJ
Ľr			$T_{j} = 150^{\circ}C$		14.1		1113

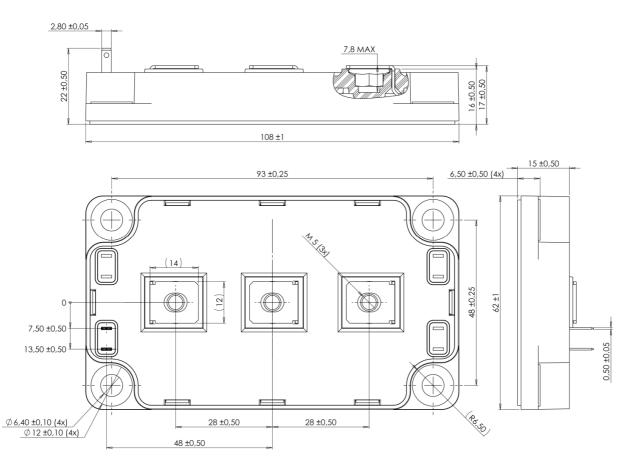


APTGT600DA60G

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.065	°C/W
R _{th} JC			Diode			0.11	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range Storage Temperature Range			-40		175	
T _{STG}				-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)



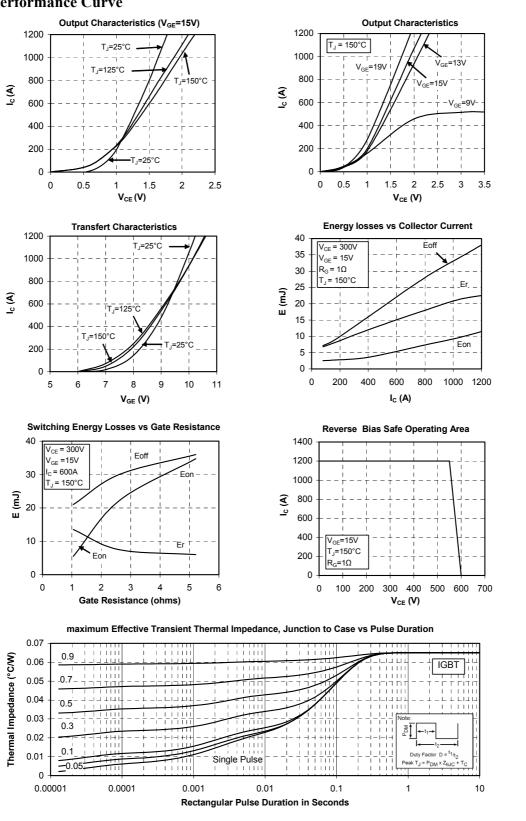
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

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Typical Performance Curve

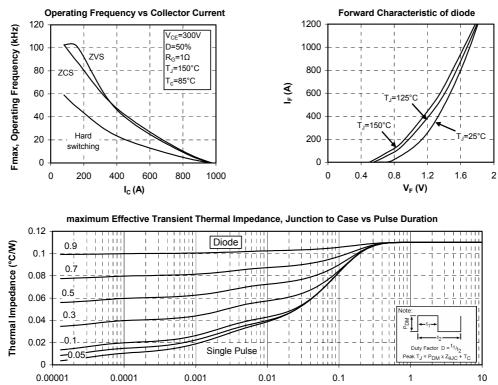




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APTGT600DA60G



Rectangular Pulse Duration in Seconds

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